

MOSFETs Silicon P-Channel MOS

# SSM6J402TU

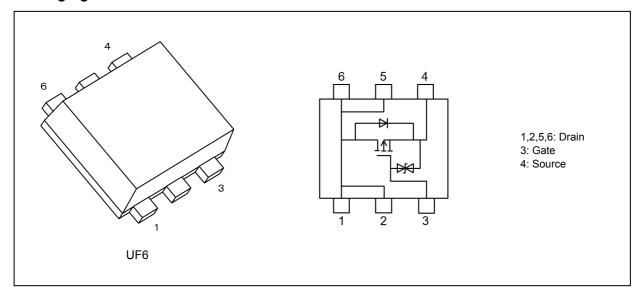
#### 1. Applications

- · DC-DC Converters
- · High-Speed Switching

#### 2. Features

- (1) 4.0-V drive
- (2) Low drain-source on-resistance
  - :  $R_{DS(ON)}$  = 225 m $\Omega$  (max) (@V<sub>GS</sub> = -4 V)  $R_{DS(ON)}$  = 117 m $\Omega$  (max) (@V<sub>GS</sub> = -10 V)

## 3. Packaging and Internal Circuit





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-30	V
Gate-source voltage		$V_{GSS}$	±20	V
Drain current (DC)		I <sub>D</sub>	-2.0	Α
Drain current (pulsed)		I <sub>DP</sub>	-4.0	
Power dissipation	(Note 1)	P <sub>D</sub>	500	mW
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Device mounted on a FR4 board.

(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad : 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

# 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 16 \text{ V}$	_	_	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	_	_	-1	μА
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-30	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 20 V	-15	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -1 mA	-1.2	_	-2.6	V
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -4 V	_	160	225	mΩ
			I <sub>D</sub> = -1 A, V <sub>GS</sub> = -10 V	_	80	117	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -1 A	1.6	3.1	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

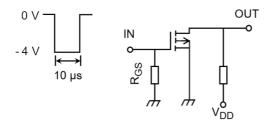
Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = 0 V,	_	280	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	45	_	
Output capacitance	Coss		_	80	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = -15 V, $I_{D}$ = -1.0 A, $V_{GS}$ = 0 to -4 V, $R_{G}$ = 10 $\Omega$	_	16	_	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%, Input: $t_r$ , $t_f$ < 5 ns Common source, See Chapter 5.3.	_	35		

#### 5.3. Switching Time Test Circuit



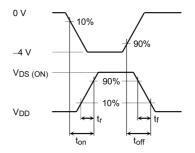


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DS}$ = -15 V, $I_{D}$ = -2.0 A,	_	5.3		nC
Gate-source charge	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	_	4.1	_	
Gate-drain charge	$Q_{gd}$		_	1.2		



# 5.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = 2.0 A, V <sub>GS</sub> = 0 V	_	0.8	1.2	V

Note 1: Pulse measurement.

#### 6. Marking

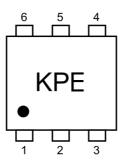
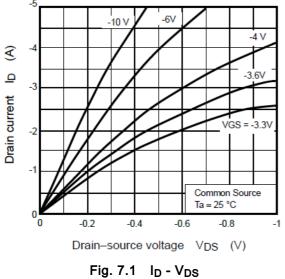
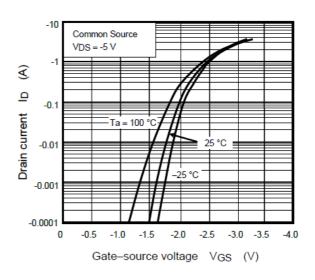


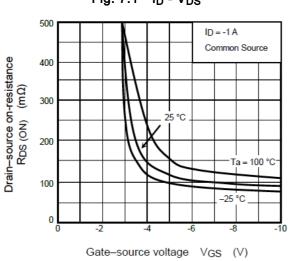
Fig. 6.1 Marking

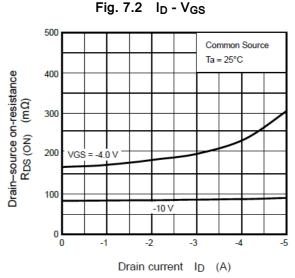


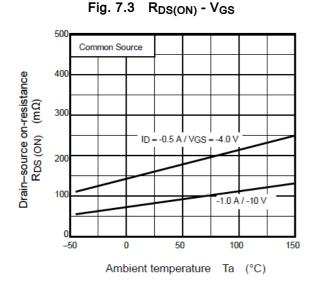
### 7. Characteristics Curves (Note)











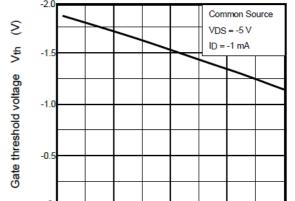


Fig. 7.4 R<sub>DS(ON)</sub> - I<sub>D</sub>

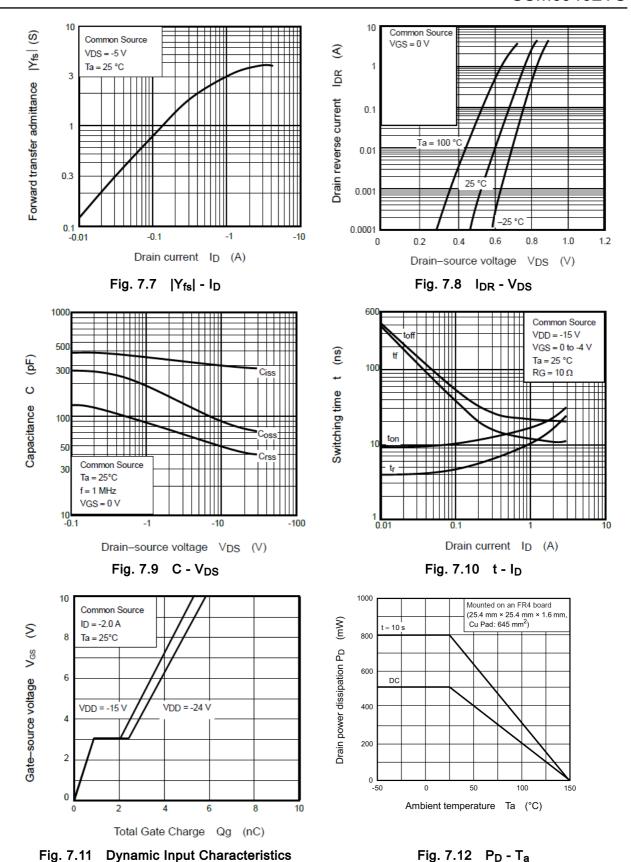
Fig. 7.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

Fig. 7.6 V<sub>th</sub> - T<sub>a</sub>

Ambient temperature Ta (°C)

-50



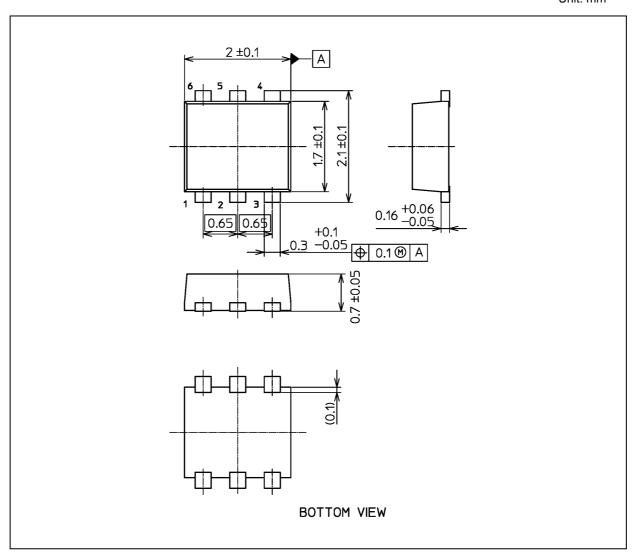


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 7.0 mg (typ.)

	Package Name(s)	
Nickname: UF6		



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